

ABSTRACT OF THE DISCLOSURE

ETCHING SOLUTION FOR SELECTIVELY REMOVING TANTALUM NITRIDE OVER TITANIUM NITRIDE DURING MANUFACTURE OF A SEMICONDUCTOR DEVICE

Described herein is an etching solution comprising water; phosphoric acid solution (aqueous); a fluoride ion source; and a water-miscible organic solvent. Such compositions are useful for the selective removal of tantalum nitride over titanium nitride from a microelectronic device having such material(s) thereon during its manufacture.

(No drawing to be published)